Guidelines for Abstract Preparation of EDISON 22  
(Bold, 12 point, Times or Times New Roman)

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A **one-page abstract** should be prepared on an A4-size paper with 2 cm margins all around and **uploaded in the pdf format**. Templates are provided in LaTeX, Word and Open Document format. Authors who prefer a different typesetting system, please adhere to the following guidelines. Please do not change the style of the abstract (font types, sizes, spacings, margins, etc.). The submission deadline is **15 March 2023**.

The abstract must include the title of the paper, author(s), affiliation(s), address(es) and e-mail address of the corresponding author. In the title capital letters should be used for the initial letter of each word except articles, prepositions and conjunctions. The main text should be typed single-spaced and at 11 point. The numbered list of all references should appear at the end of the abstract. When referring to them in the text, the reference number should be indicated by brackets, such as [1, 2]. Figures can be included; they should be numbered consecutively and accompanied by a figure caption in 10 point below the figure. Please do not generate page numbers.



Fig.1. EDISON 22 logo (caption 10 point, Times or Times New Roman)

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10. Charge dynamics in energy conversion and energy harvesting processes
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12. Interaction of charges with plasmonic, phononic and mechanical excitations

References

[1] J. Bardeen and W. H. Brattain, Phys. Rev. **75**, 1208 (1949).

[2] A. Einstein, B. Podolsky, and N. Rosen, Phys. Rev. **47**, 777 (1935).